IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A light-emitting device comprising:

a transistor formed over a substrate, the transistor being configured to be operated in a saturated region;

a first passivation film and a second passivation film;

a photosensitive organic resin film having an opening;

a light-emitting element formed between the first passivation film and the second passivation film; and

wherein the light-emitting element comprises an anode, a cathode and a light-emitting layer between the anode and the cathode;

wherein the anode is in contact with the first passivation film and electrically connected to the transistor;

wherein the interface of the anode and the first passivation film is parallel to the surface of the substrate,

wherein the cathode is in contact with the second passivation film;

wherein the anode and the photosensitive organic resin film are in contact with the first passivation film;

wherein the photosensitive organic resin film is in contact with the light-emitting layer;

wherein an angle of an interface between the photosensitive organic resin film and the light-emitting layer to the anode sequentially varies,

wherein the transistor is located below the photosensitive organic resin film and simultaneously in a periphery portion of the opening, and

wherein the light-emitting layer comprises a dopant at a concentration of 0.1 % by weight or more and 0.4 % by weight or less.

2. (Currently Amended) A light-emitting device comprising:

a transistor formed over a substrate, the transistor being configured to be operated in a saturated region;

a first passivation film and a second passivation film;

a photosensitive organic resin film having an opening; and

a light-emitting element having an anode, a cathode and a light-emitting layer between the anode and the cathode,

wherein the anode is electrically connected to the transistor,

wherein the light-emitting layer comprises copper phthalocyanine and calcium fluoride as a hole-injection material and an electron-injection material, respectively;

wherein the light-emitting layer comprises a dopant at a concentration of 0.1 % by weight or more and 0.4 % by weight or less;

wherein the anode and the photosensitive organic resin film are in contact with the first passivation film;

wherein the interface of the anode and the first passivation film is parallel to the surface of the substrate,

wherein the photosensitive organic resin film is in contact with the light-emitting layer,

wherein the cathode is in contact with the second passivation film;

wherein the anode, the cathode and the light-emitting layer are overlapped in the opening,

wherein an angle of an interface between the photosensitive organic resin film and the light-emitting layer to the anode sequentially varies,

wherein the transistor is located below the photosensitive organic resin film and simultaneously in a periphery portion of the opening, and

wherein the photosensitive organic resin film and the cathode are covered with the second passivation film.

3. (Previously Presented) A light-emitting device according to claim 2,

wherein a radius of curvature of a curve that depicts a section in the opening of the photosensitive organic resin film is in the range from 0.2 to 2μm.

4. (Original) A light-emitting device according to claim 2,

wherein the photosensitive organic resin film has positive photosensitivity.

5. (Original) A light-emitting device according to claim 2,

wherein the photosensitive organic resin film has negative photosensitivity.

6. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein at least one of the first passivation film and the second passivation film is a carbon nitride film or a silicon nitride film formed by an RF sputtering process.

7. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein at least one of the first passivation film and the second passivation film comprises a material selected from the group consisting of DLC, boron nitride and alumina.

8. (Previously Presented) A electronic equipment having the light-emitting device according to claims 1 and 2,

wherein the electronic equipment is selected from the group consisting of video cameras, digital cameras, goggle type displays, navigation systems, audio reproducing devices, laptop computers, game machines, portable information terminals, image reproducing device.

9. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting element, after turning on for 100 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 10 % or less of the initial intrinsic brightness.

10. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting element, after turning on for 1000 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 20 % or less of the initial intrinsic brightness.

11. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate, and

wherein when brightness of the light-emitting element is set at 200 nt when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 40 degree centigrade or less.

12. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate,

wherein when power consumption of the light-emitting element and the transistor is set at 600 mW when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 40 degree centigrade or less.

13. (Original) A light-emitting device as set forth in any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element;

both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device; and

the pixel portion is disposed on a substrate;

wherein when brightness of the light-emitting element is set at 130 nt when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 35 degree centigrade or less.

14. (Original) A light-emitting device according to any one of claims 1 and 2,

wherein the transistor controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate, and

wherein when power consumption of the light-emitting element and the transistor is set at 400 mW when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 35 degree centigrade or less.

15. (Original) A light-emitting device according to any one of claims 1 and 2, wherein the light-emitting layer comprises a quinacridone derivative.

16-22 (Canceled).

23. (Currently Amended) A light-emitting device comprising:

a transistor formed over a substrate;

a first passivation film and a second passivation film;

a photosensitive organic resin film having an opening; and

a light-emitting element formed between the first passivation film and the second passivation film,

wherein the light-emitting element comprises an anode, a cathode and a light-emitting layer between the anode and the cathode,

wherein the transistor is electrically connected to the anode and is configured to be operated in a saturated region,

wherein the anode and the photosensitive organic resin film are in contact with the first passivation film,

wherein the interface of the anode and the first passivation film is parallel to the surface of the substrate,

wherein the photosensitive organic resin film is in contact with the light-emitting layer,

wherein the cathode is in contact with the second passivation film,

wherein the anode, the cathode and the light-emitting layer are overlapped in the opening,

wherein an angle of an interface between the photosensitive organic resin film and the light-emitting layer to the anode sequentially varies,

wherein the transistor is located below the photosensitive organic resin film and simultaneously in a periphery portion of the opening, and

wherein the photosensitive organic resin film and the cathode are covered with the second passivation film.

24. (New) A driving method of a display device comprising a plurality of pixels each comprising a switching transistor, a current controlling transistor, and a light-emitting element,

wherein a first passivation film is formed over the switching transistor and the current controlling transistor,

wherein the light-emitting element comprises a light-emitting layer formed between a first electrode and a second electrode and is formed over the first passivation film,

wherein the first electrode is in contact with the first passivation film,

wherein a photosensitive organic resin film having an opening is formed over the first passivation film and is in contact with the first passivation film and the light-emitting layer,

wherein a second passivation film is formed over the light-emitting element and in contact with the second electrode,

wherein the switching transistor and the current controlling transistor are located in a periphery portion of the opening of the photosensitive organic resin film ,

wherein the light-emitting layer comprises a dopant at a concentration of 0.1% by weight or more and 0.4% by weight or less, and

wherein the driving transistor is operated in a saturated region.

25. (New) A driving method of a display device according to claim 24,

wherein the first passivation film comprises a material selected from DLC, boron nitride, alumina, carbon nitride, and silicon nitride.

26. (New) A driving method of a display device according to claim 24,

wherein an angle of an interface between the photosensitive organic resin film and the light-emitting layer to the anode sequentially varies.

27. (New) A driving method of a display device according to claim 24,

wherein a radius of curvature of a curve that depicts a section in the opening of the photosensitive organic resin film is in the range from 0.2 to 2μm.

28. (New) A driving method of a display device according to claim 24,

wherein the dopant is a quinacridone derivative.

29. (New) A driving method of a display device according to claim 24,

wherein the interface of the anode and the first passivation film is parallel to the surface of the substrate,

30. (New) A driving method of a display device comprising a plurality of pixels each comprising a switching transistor, a current controlling transistor, and a light-emitting element,

wherein a first passivation film is formed over the switching transistor and the current controlling transistor,

wherein the light-emitting element comprises a light-emitting layer formed between a first electrode and a second electrode and is formed over the first passivation film,

wherein the first electrode is in contact with the first passivation film,

wherein a photosensitive organic resin film having an opening is formed over the first passivation film and is in contact with the first passivation film and the light-emitting layer,

wherein a second passivation film is formed over the light-emitting element and in contact with the second electrode,

wherein the switching transistor and the current controlling transistor are located in a periphery portion of the opening of the photosensitive organic resin film, and

wherein the driving transistor is operated in a saturated region.

31. (New) A driving method of a display device according to claim 30,

wherein the first passivation film comprises a material selected from DLC, boron nitride, alumina, carbon nitride, and silicon nitride.

32. (New) A driving method of a display device according to claim 30,

wherein an angle of an interface between the photosensitive organic resin film and the light-emitting layer to the anode sequentially varies.

33. (New) A driving method of a display device according to claim 30,

wherein a radius of curvature of a curve that depicts a section in the opening of the photosensitive organic resin film is in the range from 0.2 to 2μm.

34. (New) A driving method of a display device according to claim 30,

wherein the dopant is a quinacridone derivative.

35. (New) A driving method of a display device according to claim 30,

wherein the interface of the anode and the first passivation film is parallel to the surface of the substrate.